

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

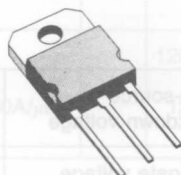
TYPE	V _{DSS}	R _{DS(on)}	I _D
BUZ354	500 V	0.8 Ω	8 A

- HIGH SPEED SWITCHING
- HIGH VOLTAGE - 500V FOR OFF-LINE SMPS
- HIGH CURRENT - 8A FOR UP TO 200W SMPS
- ULTRA FAST SWITCHING - FOR OPERATION AT < 100KHz
- EASY DRIVE - FOR REDUCED COST AND SIZE

INDUSTRIAL APPLICATIONS:

- SWITCHING POWER SUPPLIES
- MOTOR CONTROLS

N - channel enhancement mode POWER MOS field effect transistor. Easy drive and very fast switching times make this POWER MOS transistor ideal for high speed switching applications. Typical uses include switching mode power supplies, uninterruptible power supplies and motor speed control.


TO-218
**INTERNAL SCHEMATIC
DIAGRAM**

ABSOLUTE MAXIMUM RATINGS

V _{DS}	Drain-source voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate voltage (R _{GS} = 20 KΩ)	500	V
V _{GS}	Gate-source voltage	± 20	V
I _D	Drain current (continuous) T _c = 25°C	8	A
I _{DM}	Drain current (pulsed)	32	A
P _{tot}	Total dissipation at T _c < 25°C	125	W
T _{stg}	Storage temperature	- 55 to 150	°C
T _j	Max. operating junction temperature	150	°C
	DIN humidity category (DIN 40040)	E	
	IEC climatic category (DIN IEC 68-1)	55/150/56	

THERMAL DATA

$R_{thj - case}$	Thermal resistance junction-case	max	1.0	°C/W
$R_{thj - amb}$	Thermal resistance junction-ambient	max	45	°C/W

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
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OFF

$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$	$V_{GS} = 0$	500		V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$	$V_{DS} = \text{Max Rating}$		250	μA
			$T_j = 125^\circ\text{C}$		1000	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA

ON

$V_{GS (th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	$I_D = 1 \text{ mA}$	2.1	4	V
$R_{DS (on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$	$I_D = 5.5 \text{ A}$		0.8	Ω

DYNAMIC

g_{fs}	Forward transconductance	$V_{DS} = 25 \text{ V}$	$I_D = 5.5 \text{ A}$	2.7		mho
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$	$f = 1 \text{ MHz}$		4900	pF
C_{oss}	Output capacitance				400	pF
C_{rss}	Reverse transfer capacitance				170	pF

SWITCHING

$t_{d (on)}$	Turn-on time	$V_{DD} = 30 \text{ V}$	$I_D = 2.8 \text{ A}$		75	ns
t_r	Rise time	$R_{GS} = 50 \Omega$	$V_{GS} = 10 \text{ V}$		120	ns
$t_{d (off)}$	Turn-off delay time				430	ns
t_f	Fall time				140	ns

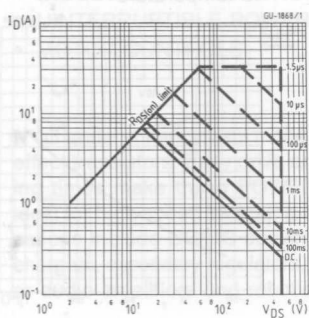
ELECTRICAL CHARACTERISTICS (Continued)

Parameters		Test Conditions		Min.	Typ.	Max.	Unit
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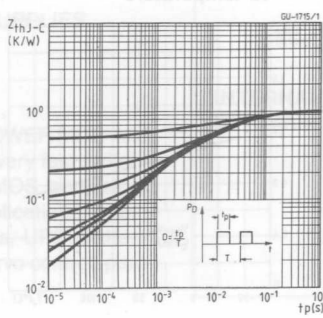
SOURCE DRAIN DIODE

I_{SD}	Source-drain current	$T_c = 25^\circ\text{C}$				8	A
I_{SDM}	Source-drain current (pulsed)					32	A
V_{SD}	Forward on voltage	$I_{SD} = 16\text{ A}$	$V_{GS} = 0$			1.6	V
t_{rr}	Reverse recovery time				1200		ns
Q_{rr}	Reverse recovered charge	$I_{SD} = 8\text{ A}$	$di/dt = 100\text{A}/\mu\text{s}$		12		μC

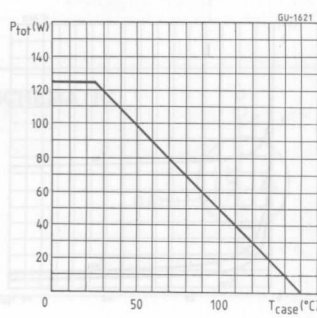
Safe operating areas



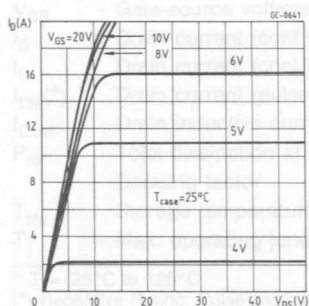
Thermal impedance



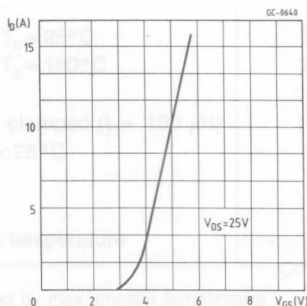
Derating curve



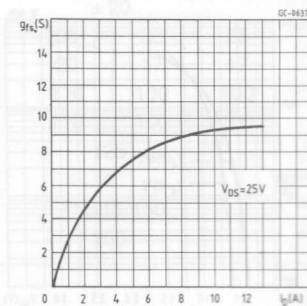
Output characteristics



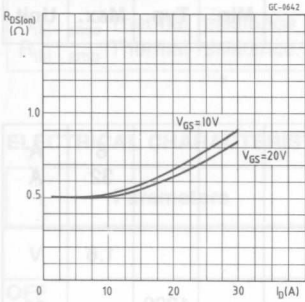
Transfer characteristics



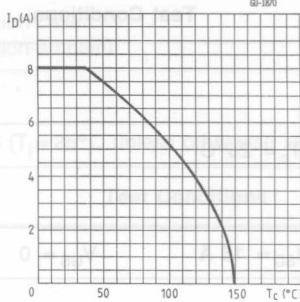
Transconductance



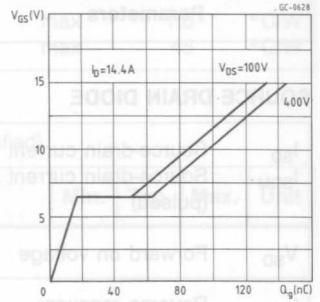
Static drain-source on resistance



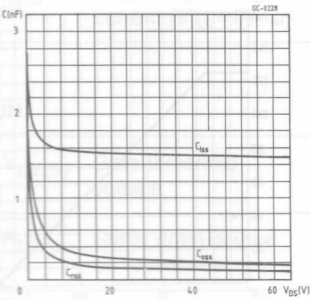
Maximum drain current vs temperature



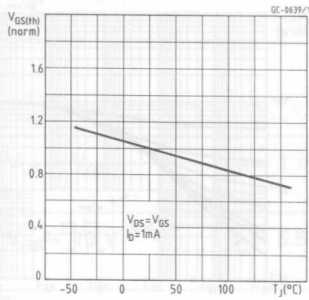
Gate charge vs gate-source voltage



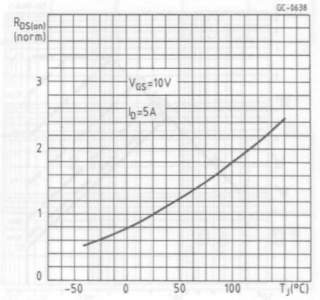
Capacitance variation



Gate threshold voltage vs temperature



Drain-source on resistance vs temperature



Source-drain diode forward characteristics

